Power MOSFET 200 mA, 50 V

N-Channel SOT-23

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low Threshold Voltage (V_{GS(th)}: 0.5 V-1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	50	Vdc
Gate-to-Source Voltage - Continuous	V _{GS}	± 20	Vdc
Drain Current - Continuous @ $T_A = 25^{\circ}C$ - Pulsed Drain Current $(t_p \le 10 \ \mu s)$	I _D	200 800	mA
Total Power Dissipation @ T _A = 25°C	P _D	225	mW
Operating and Storage Temperature Range	T _J , T _{stg}	– 55 to 150	ç
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	TL	260	°C

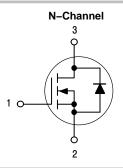
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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200 mA, 50 V $R_{DS(on)} = 3.5 Ω$





SOT-23 CASE 318 STYLE 21

> J1 M



1 L] = Device Code = Date Code*

= Pb-Free Package
 (Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS138LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BVSS138LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BSS138LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
BVSS138LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

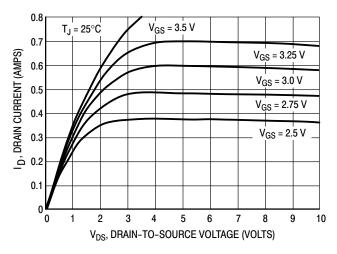
Chai	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltag (V _{GS} = 0 Vdc, I _D = 250 μAdc)	V _{(BR)DSS}	50	_	_	Vdc	
Zero Gate Voltage Drain Current $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C})$ $(V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C})$ $(V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 150^{\circ}\text{C})$	I _{DSS}	- - -	- - -	0.1 0.5 5.0	μAdc	
Gate-Source Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc)		I _{GSS}	_	_	±0.1	μAdc
ON CHARACTERISTICS (Note 1)						
Gate-Source Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	V _{GS(th)}	0.85	_	1.5	Vdc	
Static Drain–to–Source On–Resistance $ (V_{GS}=2.75~\text{Vdc},~I_D<200~\text{mAdc},~T_A=-40^{\circ}\text{C to }+85^{\circ}\text{C}) \\ (V_{GS}=5.0~\text{Vdc},~I_D=200~\text{mAdc}) $		r _{DS(on)}		5.6 -	10 3.5	Ω
Forward Transconductance (V _{DS} = 25 Vdc, I _D = 200 mAdc, f = 1.0 kHz)		9fs	100	-	_	mmhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{iss}	_	40	50	pF
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ MHz})$	C _{oss}	_	12	25	1
Transfer Capacitance	(V _{DG} = 25 Vdc, V _{GS} = 0, f = 1 MHz)	C _{rss}	_	3.5	5.0	1
SWITCHING CHARACTERISTICS (N	ote 2)					
Turn-On Delay Time	()/ 20)/4-1 02.44-)	t _{d(on)}	_	_	20	ns
Turn-Off Delay Time	$(V_{DD} = 30 \text{ Vdc}, I_D = 0.2 \text{ Adc},)$	t _{d(off)}	_	_	20	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

2. Switching characteristics are independent of operating junction temperature.

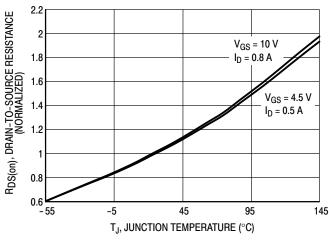
TYPICAL ELECTRICAL CHARACTERISTICS



0.9 25°C $V_{DS} = 10 V$ 0.8 -55°C ID, DRAIN CURRENT (AMPS) 0.7 150°C 0.6 0.5 0.4 0.3 0.2 0.1 0.5 4.5 VGS, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



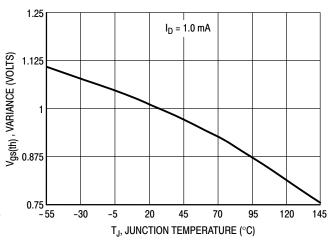
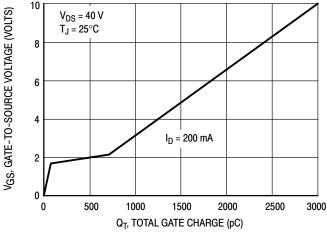


Figure 3. On–Resistance Variation with Temperature

Figure 4. Threshold Voltage Variation with Temperature



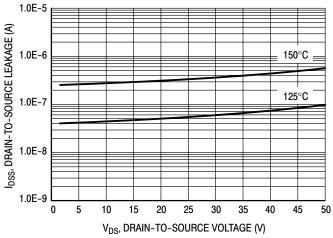
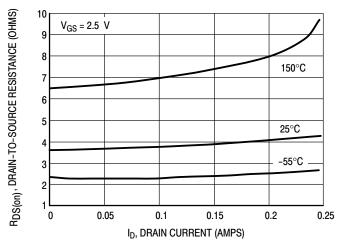


Figure 5. Gate Charge

Figure 6. IDSS

TYPICAL ELECTRICAL CHARACTERISTICS



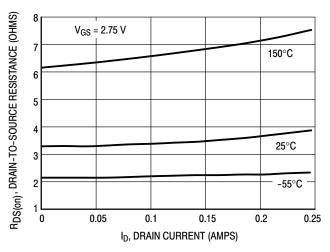
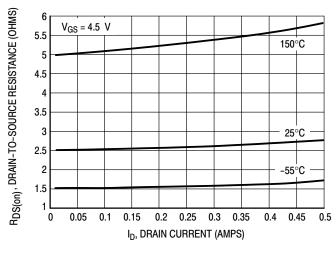


Figure 7. On-Resistance versus Drain Current

Figure 8. On-Resistance versus Drain Current



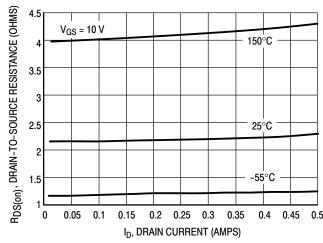
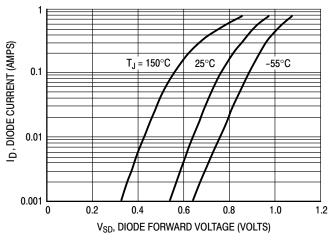


Figure 9. On-Resistance versus Drain Current

Figure 10. On-Resistance versus Drain Current



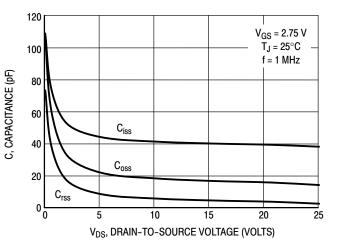


Figure 11. Body Diode Forward Voltage

Figure 12. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

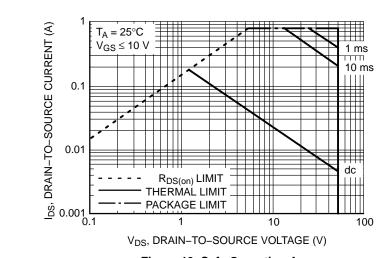
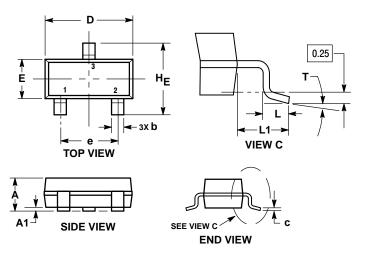


Figure 13. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
- I DISE MATERIAL.

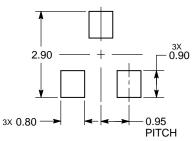
 DIMENSIONS O AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS					
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

STYLE 21:

- PIN 1. GATE
 - 2. SOURCE
 - 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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